

2N5769



NPN Switching Transistor

This device is designed for high speed saturated switching applications at currents to 100 mA. Sourced from Process 21. See PN2369A for characteristics.

Absolute Maximum Ratings*

TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units	
V_{CEO}	Collector-Emitter Voltage	15	V	
V _{CBO}	Collector-Base Voltage	40	V	
V_{EBO}	Emitter-Base Voltage	4.5	V	
Ic	Collector Current - Continuous	200	mA	
T _J , T _{stg}	Operating and Storage Junction Temperature Range	-55 to +150	°C	

^{*}These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

1) These ratings are based on a maximum junction temperature of 150 degrees C.

2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Thermal Characteristics

TA = 25°C unless otherwise noted

Symbol	Characteristic	Max	Units
		2N5769	
P _D	Total Device Dissipation Derate above 25°C	350 2.8	mW mW/°C
$R_{\theta JC}$	Thermal Resistance, Junction to Case	125	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	357	°C/W

NPN Switching Transistor (continued)

Symbol	Parameter	Test Conditions	Min	Max	Units
o== 0	D.4.075D10710.0				
	RACTERISTICS	T			
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage*	$I_C = 10 \text{ mA}, I_B = 0$	15		V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	$I_C = 10 \mu\text{A}, I_E = 0$	40		V
V _{(BR)EBO}	Emitter-Base Breakdown Voltage	$I_E = 10 \mu A, I_C = 0$	4.5		V
$V_{(BR)CES}$	Collector-Emitter Breakdown Voltage	$I_{C} = 10 \mu\text{A}, I_{B} = 0$	40		V
І _{сво}	Collector Cutoff Current	$V_{CB} = 20 \text{ V}, I_{E} = 0$ $V_{CB} = 20 \text{ V}, I_{E} = 0, T_{A} = 125 ^{\circ}\text{C}$		0.4 30	μA μA
I _{CES}	Collector Cutoff Current	$V_{CE} = 20 \text{ V}, I_{B} = 0$		0.4	μΑ
I _{EBO}	Emitter Cutoff Current	$V_{EB} = 4.5 \text{ V}, I_{C} = 0$		1.0	μΑ
ĴFE	DC Current Gain	$I_C = 10 \text{ mA}, V_{CE} = 0.35 \text{ V}$ $I_C = 10 \text{ mA}, V_{CE} = 0.35 \text{ V}$ $T_A = -55 ^{\circ}\text{C}$ $I_C = 30 \text{ mA}, V_{CE} = 0.40 \text{ V}$	40 20 30	120	
			20		
		$I_C = 30 \text{ mA}, V_{CE} = 0.40 \text{ V}$ $I_C = 100 \text{ mA}, V_{CE} = 1.0 \text{ V}$	30 20		
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = 10 \text{ mA}, I_B = 1.0 \text{ mA}$ $I_C = 10 \text{ mA}, I_B = 1.0 \text{ mA}$		0.2	V
		T _A = 125 °C		0.3	V
		$I_C = 30 \text{ mA}, I_B = 3.0 \text{ mA}$ $I_C = 100 \text{ mA}, I_B = 10 \text{ mA}$		0.25 0.5	V V
V _{BE(sat)}	Base-Emitter Saturation Voltage	$I_C = 10 \text{ mA}, I_B = 1.0 \text{ mA}$ $I_C = 10 \text{ mA}, I_B = 1.0 \text{ mA}$ $I_C = 10 \text{ mA}, I_B = 1.0 \text{ mA}$	0.7	0.85	V
		$T_A = 125 ^{\circ}\text{C}$ $I_C = 10 \text{mA}, I_B = 1.0 \text{mA}$	0.59	1.02	V
		T _A = - 55 °C	0.59	1.02	V
		$I_C = 30 \text{ mA}, I_B = 3.0 \text{ mA}$		1.15	V V
	IGNAL CHARACTERISTICS	I _C = 100 mA, I _B = 10 mA		1.6	l v
C _{cb}	Collector-Base Capacitance	V _{CB} = 5.0 V, f = 1.0 MHz		4.0	pF
h _{fe}	Small-Signal Current Gain	$I_C = 10 \text{ mA}, V_{CE} = 10 \text{ V},$ f = 100 MHz	5.0		
SWITCHI	NG CHARACTERISTICS				
ton	Turn-on Time	I _C = 10 mA,		12	ns
t _{off}	Turn-off Time	$I_{B1} = 3.0 \text{ mA}, I_{B2} = 1.5 \text{ mA}$		18	ns
	Storage Time	$I_C = I_{B1} = I_{B2} = 10 \text{ mA}$			

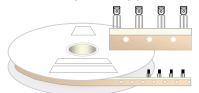
^{*}Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2.0%

TO-92 Tape and Reel Data FAIRCHILD SEMICONDUCTOR TM **TO-92 Packaging** Configuration: Figure 1.0 **TAPE and REEL OPTION** FSCINT Label sample See Fig 2.0 for various Reeling Styles CBVK//418019 **FSCINT** Label 5 Reels per Intermediate Box Customized F63TNR Label sample Label F63TNR LOT: CBVK741B019 QTY: 2000 FSID: PN222N Customized QTY1: QTY2: Label 375mm x 267mm x 375mm Intermediate Box TO-92 TNR/AMMO PACKING INFROMATION **AMMO PACK OPTION** See Fig 3.0 for 2 Ammo Packing Style Quantity EOL code **Pack Options** 2,000 D26Z Е 2,000 D27Z Ammo М 2,000 D74Z D75Z 2,000 **FSCINT** Unit weight = 0.22 gm Reel weight with components = 1.04 kg Ammo weight with components = 1.02 kg Max quantity per intermediate box = 10,000 units Label 5 Ammo boxes per Intermediate Box 327mm x 158mm x 135mm Immediate Box Customized F63TNR Customized Label Label 333mm x 231mm x 183mm Intermediate Box (TO-92) BULK PACKING INFORMATION **BULK OPTION** See Bulk Packing DESCRIPTION QUANTITY Information table J18Z TO-18 OPTION STD 2.0 K / BOX Anti-static Bubble Sheets TO-5 OPTION STD NO LEAD CLIP 1.5 K / BOX J05Z **FSCINT Label** NO EOL TO-92 STANDARD STRAIGHT FOR: PKG 92, NO LEADCLIP 2.0 K / BOX 94 (NON PROELECTRON SERIES), 96 TO-92 STANDARD STRAIGHT FOR: PKG 94 (PROELECTRON SERIES BCXXX, BFXXX, BSRXXX), 97, 98 L34Z NO LEADCLIP 2.0 K / BOX 2000 units per 114mm x 102mm x 51mm EO70 box for std option Immediate Box 5 EO70 boxes per intermediate Box 530mm x 130mm x 83mm Customized Intermediate box Label FSCINT Label 10,000 units maximum per intermediate box for std option

TO-92 Tape and Reel Data, continued

TO-92 Reeling Style Configuration: Figure 2.0

Machine Option "A" (H)

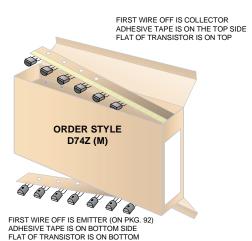


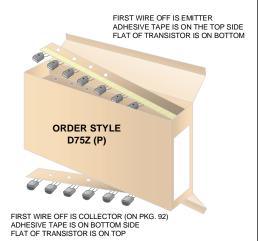
Style "A", D26Z, D70Z (s/h)

Machine Option "E" (J)

Style "E", D27Z, D71Z (s/h)

TO-92 Radial Ammo Packaging Configuration: Figure 3.0



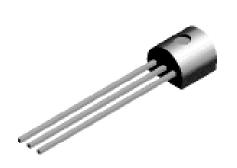


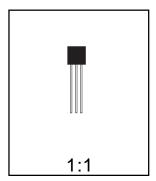


TO-92 Package Dimensions



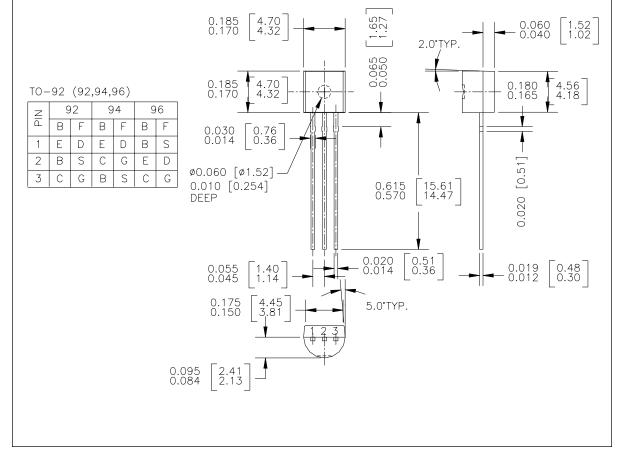
TO-92 (FS PKG Code 92, 94, 96)





Scale 1:1 on letter size paper
Dimensions shown below are in:
inches [millimeters]

Part Weight per unit (gram): 0.1977



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